优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_C = +25°C
-40V	45mΩ @ V_{GS} = -10V	-20A
	55mΩ @ V_{GS} = -4.5V	-18A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- DC-DC Converters
- Power Management Functions

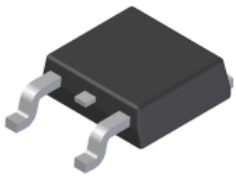
Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed

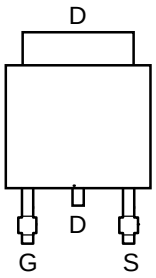
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

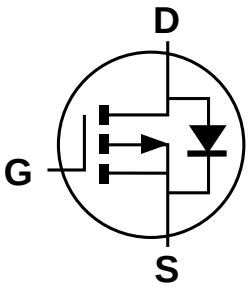
TO252 (DPAK)



Top View



Top View
Pin-Out



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-40	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T_C = +25°C T_C = +100°C	I_D	-20 -12.7	A
Maximum Body Diode Continuous Current			I_S	-2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-40	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	-18	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	16	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.6	W
	T_A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	77	°C/W
	t<10s		34	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.7	W
	T_A = +70°C		1.7	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	47	°C/W
	t<10s		30	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	4.8	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-40	–	–	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	–	–	-1	µA	V_{DS} = -40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	–	–	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0	–	-3.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	–	33	45	mΩ	V_{GS} = -10V, I_D = -4.4A
			40	55		V_{GS} = -4.5V, I_D = -3.7A
Diode Forward Voltage	V_{SD}	–	-0.75	-1.2	V	V_{GS} = 0V, I_S = -3.9A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	–	1328	–	pF	V_{DS} = -20V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	–	103	–	pF	
Reverse Transfer Capacitance	Crss	–	81	–	pF	
Gate Resistance	R_G	–	7.7	–	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Qg	–	11.2	–	nC	V_{DS} = -20V, I_D = -4.9A
Total Gate Charge (V_{GS} = -10V)	Qg	–	23.2	–	nC	
Gate-Source Charge	Qgs	–	3.3	–	nC	
Gate-Drain Charge	Qgd	–	3.9	–	nC	
Turn-On Delay Time	$t_{D(ON)}$	–	18.5	–	ns	V_{DS} = -20V, I_D = -3.9A, V_{GS} = -4.5V, R_G = 1Ω
Turn-On Rise Time	t_R	–	28.2	–	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	–	38.8	–	ns	
Turn-Off Fall Time	t_F	–	28.6	–	ns	
Body Diode Reverse Recovery Time	t_{RR}	–	15.4	–	ns	I_F = -3.9A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	–	5.4	–	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

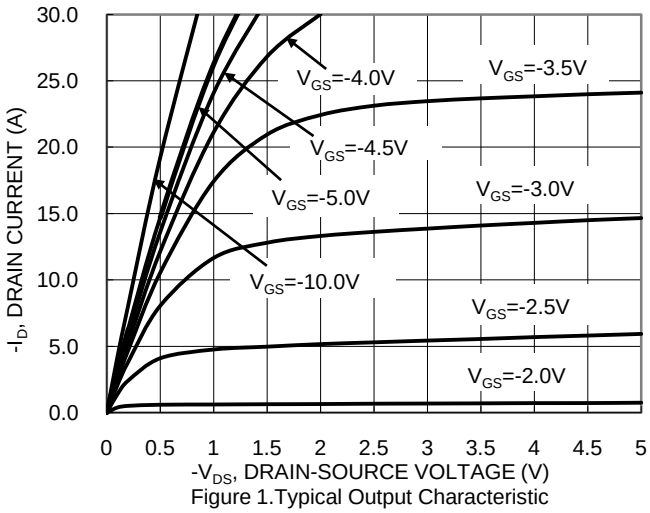


Figure 1.Typical Output Characteristic

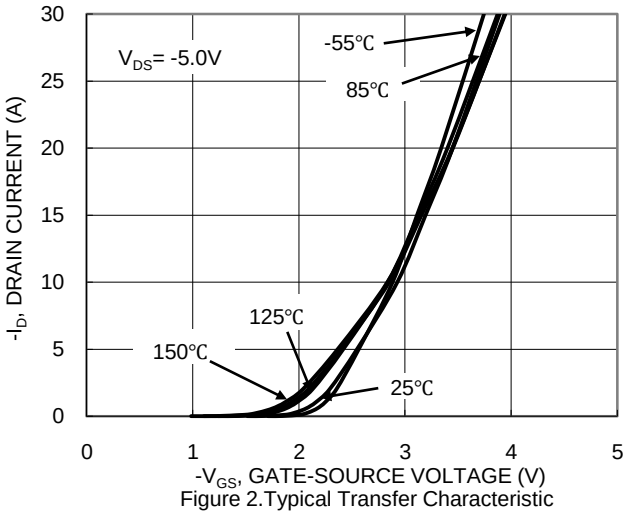


Figure 2.Typical Transfer Characteristic

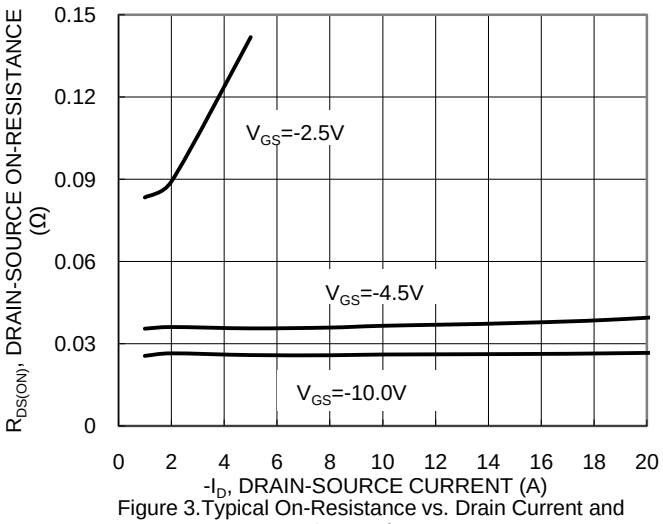


Figure 3.Typical On-Resistance vs. Drain Current and Gate Voltage

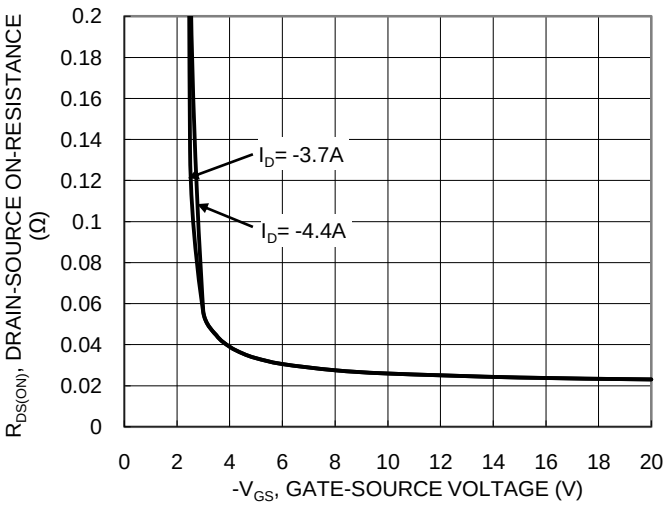


Figure 4. Typical On-Resistance vs. Gate Voltage

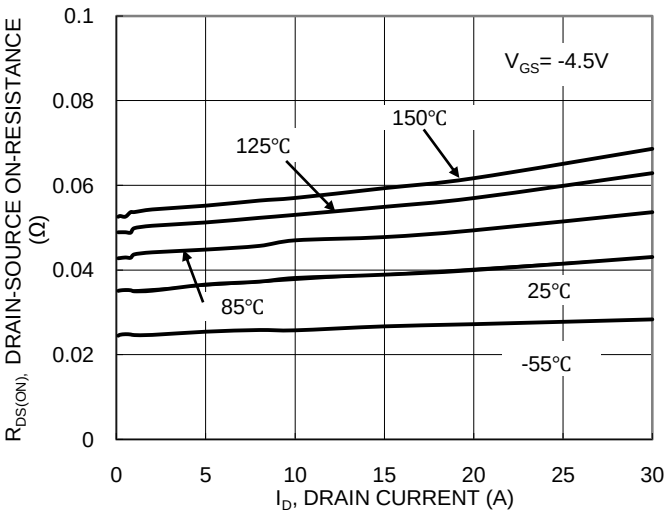


Figure 5.Typical On-Resistance vs. Drain Current and Temperature

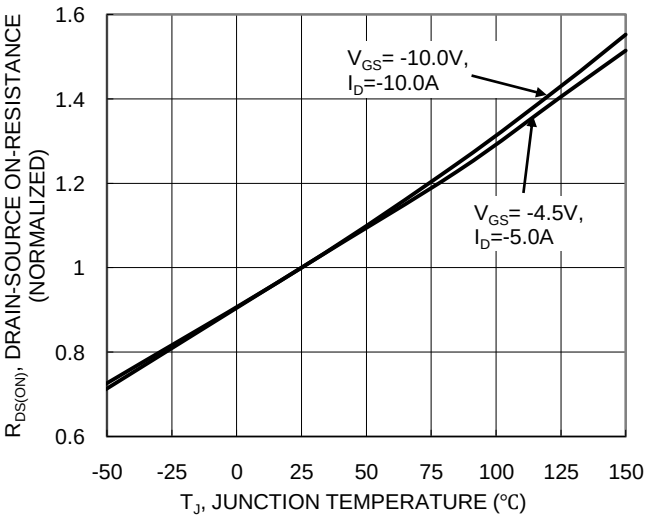


Figure 6. On-Resistance Variation with Temperature

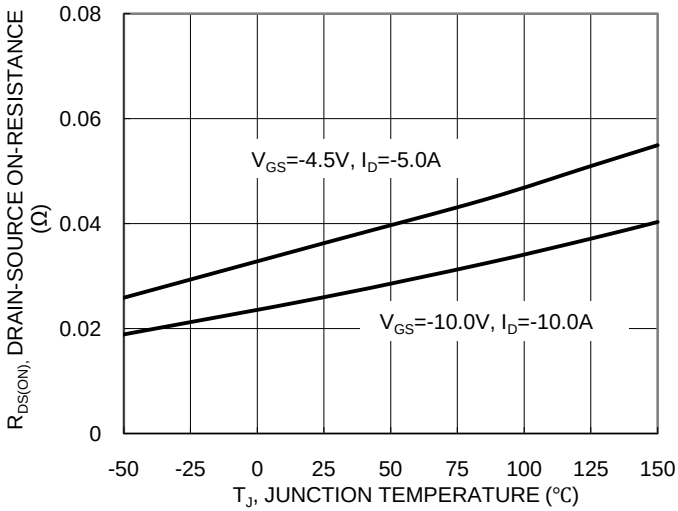


Figure 7. On-Resistance Variation with Temperature

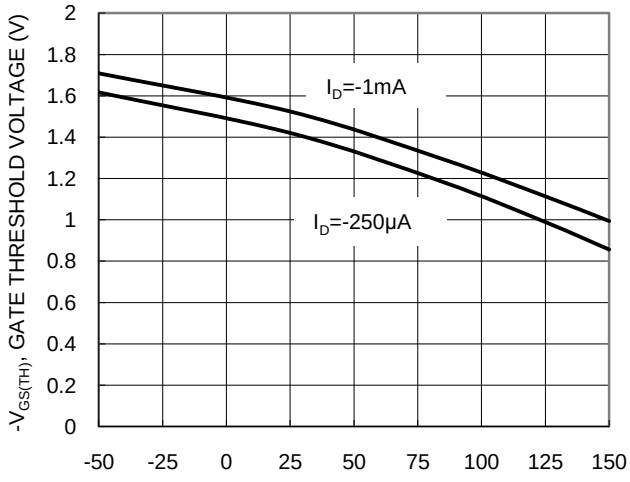


Figure 8. Gate Threshold Variation vs. Junction Temperature

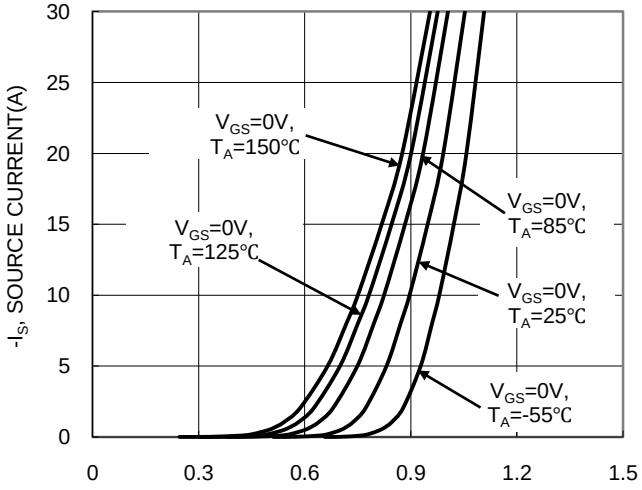


Figure 9. Diode Forward Voltage vs. Current

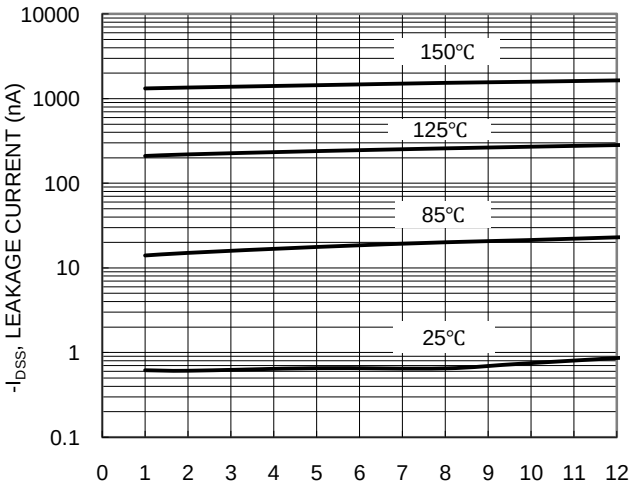


Figure 10.Typical Drain-Source Leakage Current vs. Voltage

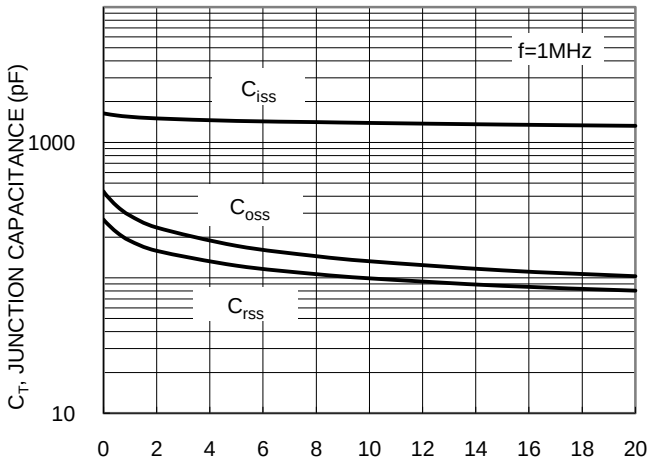


Figure 11.Typical Junction Capacitance

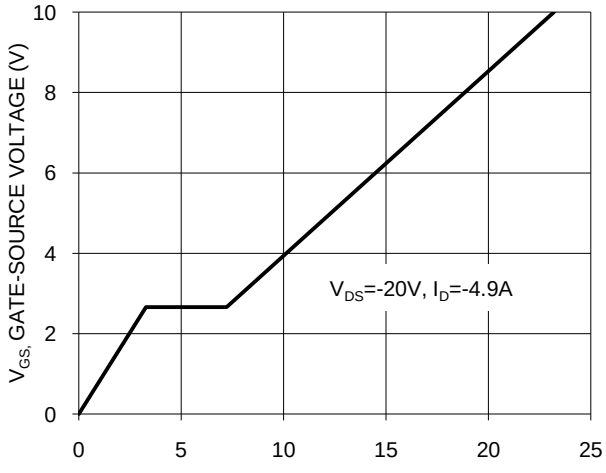


Figure 12.Gate Charge

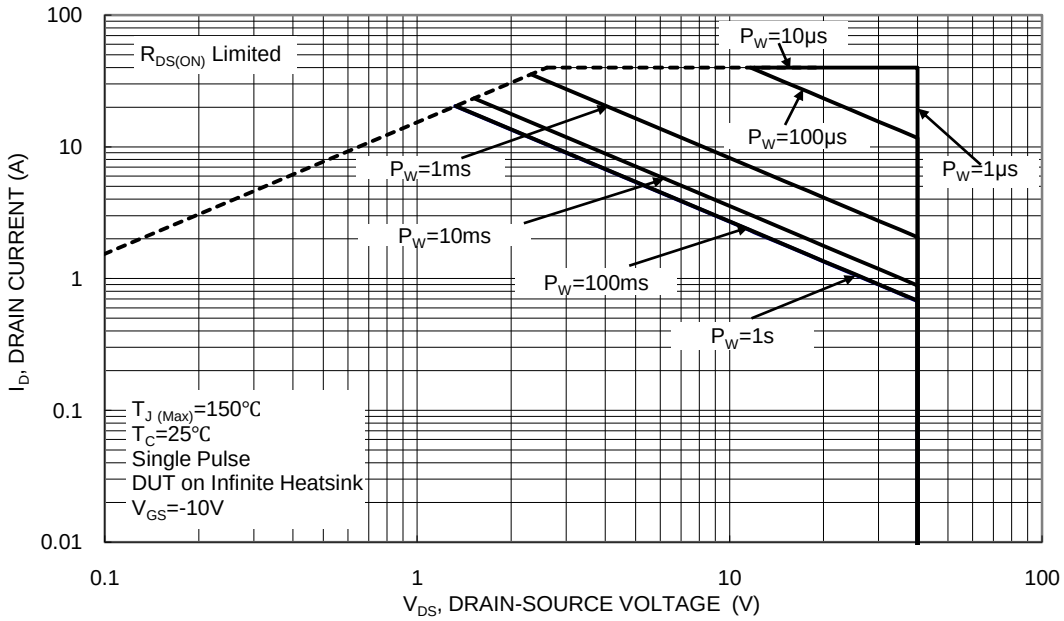


Figure 13. SOA, Safe Operation Area

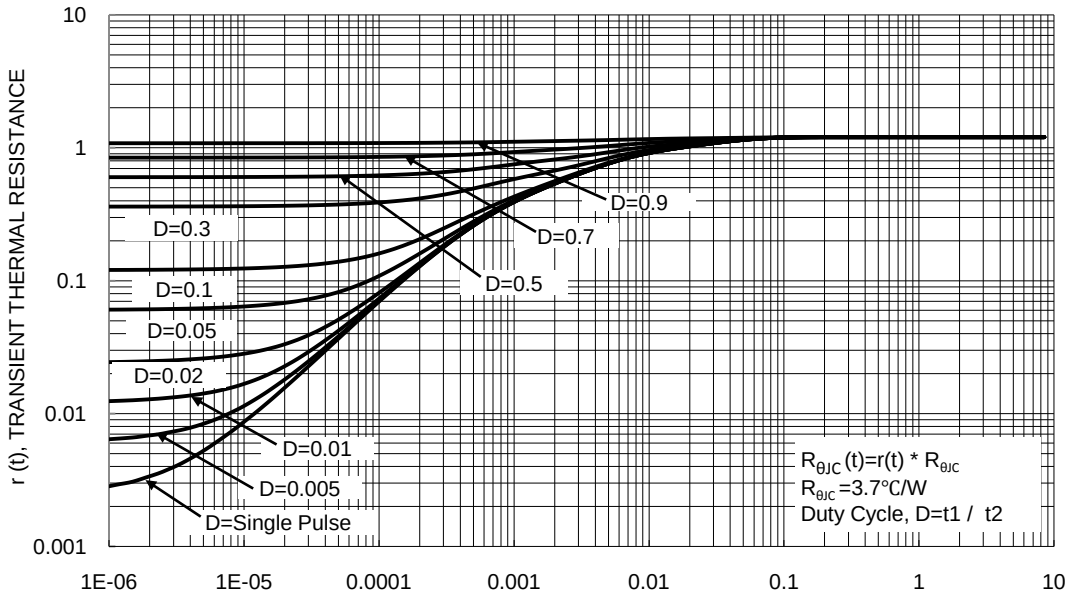
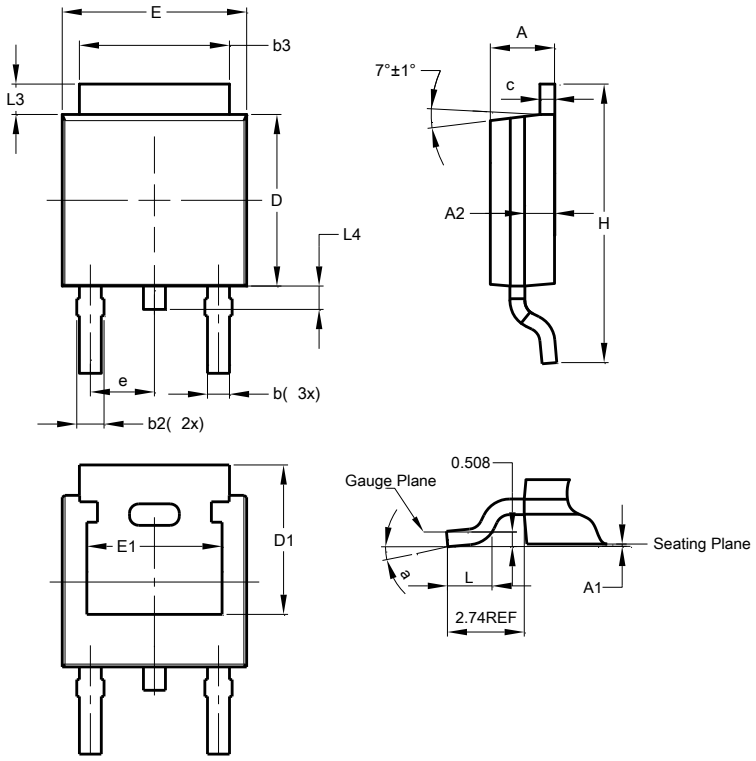


Figure 14. Transient Thermal Resistance

Package Outline Dimensions

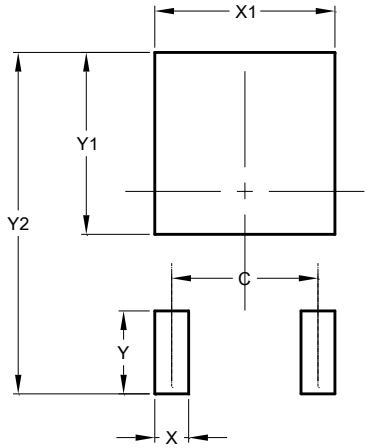
TO252 (DPAK)



TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700